



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{SSS}	R _{SS(ON)} T _{py}	I _{S Max} T _A = +25°C
14.5V	$4.8 \text{m}\Omega$ @ $V_{GS} = 3.8 \text{V}$	16.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{SS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Battery Management
- Load Switch
- Battery Protection

Features

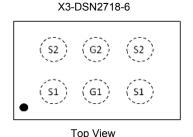
- CSP with Footprint 2.70mm × 1.81mm
- Height = 0.21mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

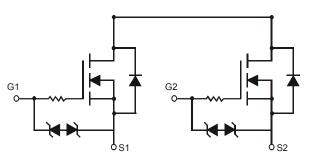
 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: X3-DSN2718-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiAu or NiPdAu.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0026 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

-			
	Part Number	Case	Packaging
	DMN15M3UCA6-7	X3-DSN2718-6	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



J2 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	20)21	2022	2023	3	20	024	2025	202	26	2027
Code	G	Н		I	J	K			L	М	N	l	0
Month	Jan	Feb	Mar	Apr	May	Jun	Ju	ıl	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	,	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Source-Source Voltage			Vsss	14	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Source Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Is	16.5 13.5	Α
Continuous Source Current (Note 5) V _{GS} = 2.5V	Is	14.2 11.3	Α		
Pulsed Source Current (Note 6)	I _{SM}	80	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P _D	1.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	$R_{\Theta JA}$	124.6	°C/W
Power Dissipation (Note 5)	P _D	2.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\Theta JA}$	51.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

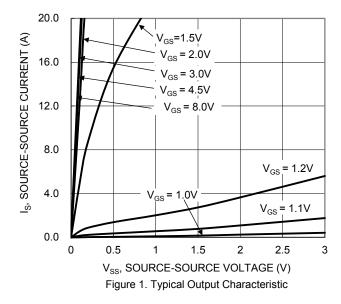
Characteristic	Cumbal	Min	Tim	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition
, ,	D) (44.5			17	lv 0/1 1 1
Source-Source Breakdown Voltage	BV _{SSS}	14.5	_		V	$V_{GS} = 0V$, $I_S = 1mA$
Zero Gate Voltage Drain Current T _J = +25°C	I _{SSS}	_	_	1	μA	$V_{SS} = 10V V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8V, V_{SS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.9	1.3	V	Vss = 6V, Is = 1mA
		3.5	4.6	5.8		$V_{GS} = 4.5V, I_S = 3A$
		3.6	4.7	5.9		$V_{GS} = 4.0V, I_{S} = 3A$
Static Source-Source On-Resistance	R _{SS(ON)}	3.8	4.8	6.2	mΩ	$V_{GS} = 3.8V, I_{S} = 3A$
		3.8	5.1	6.9		$V_{GS} = 3.1V, I_S = 3A$
		3.9	5.8	8.0		$V_{GS} = 2.5V, I_S = 3A$
Diode Forward Voltage	V _{SS}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 3A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	l	2360	1)/ O)/)/ O)/
Output Capacitance	Coss	_	666	_	pF	$V_{SS} = 6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	325	-		1 - 1.0101112
Total Gate Charge	Qg	_	35.2	_		
Gate-Source Charge	Q_{gs}	l	7.0	1	nC	$V_{SS} = 6V, V_{GS} = 4.5V,$
Gate-Drain Charge	Q_{gd}	_	8.3	_	IIC	I _S = 18A
Gate Charge at V _{TH}	$Q_{g(TH)}$	_	4.2	_		
Turn-On Delay Time	t _{D(ON)}	_	615	_	_	
Turn-On Rise Time	t _R	-	1447	_	ns	$V_{SS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	2736		115	I _S = 3A
Turn-Off Fall Time	t _F		3812	_		

Notes:

- Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
 Repetitive rating, pulse width limited by junction temperature.
 Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.







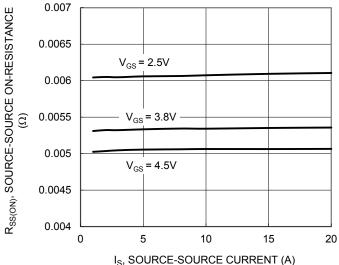


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

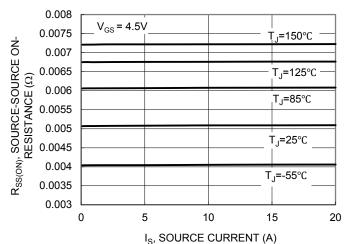


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

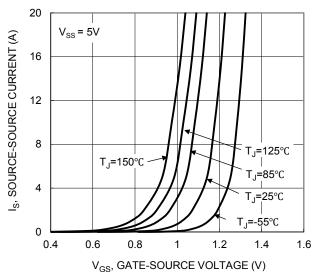


Figure 2. Typical Transfer Characteristic

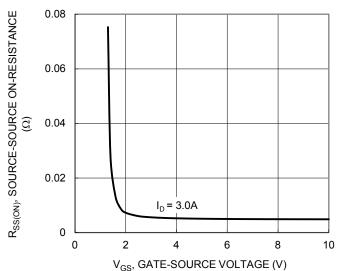


Figure 4. Typical Transfer Characteristic

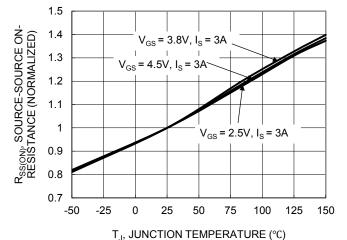


Figure 6. On-Resistance Variation with Junction Temperature





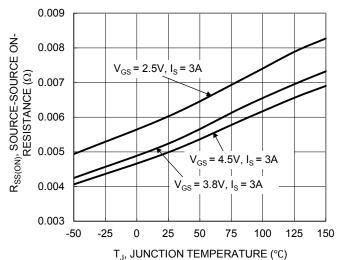
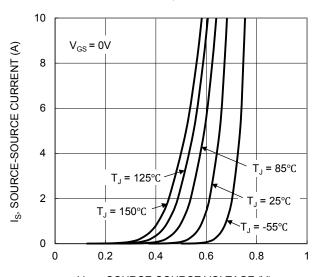


Figure 7. On-Resistance Variation with Junction Temperature



V_{FSS}, SOURCE-SOURCE VOLTAGE (V)
Figure 9. Diode Forward Voltage vs. Current

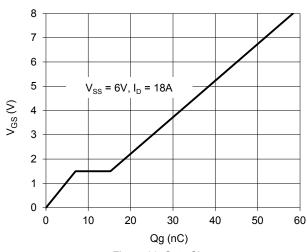


Figure 11. Gate Charge

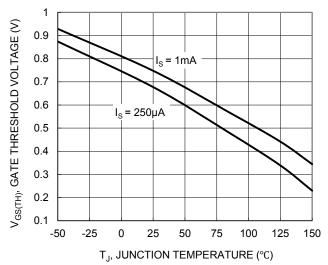


Figure 8. Gate Threshold Variation vs. Junction Temperature

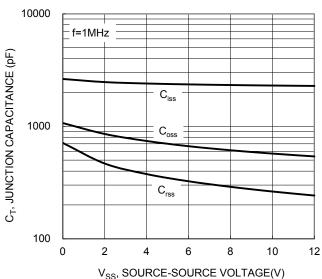


Figure 10. Typical Junction Capacitance

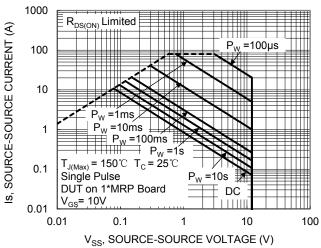


Figure 12. SOA, Safe Operation Area



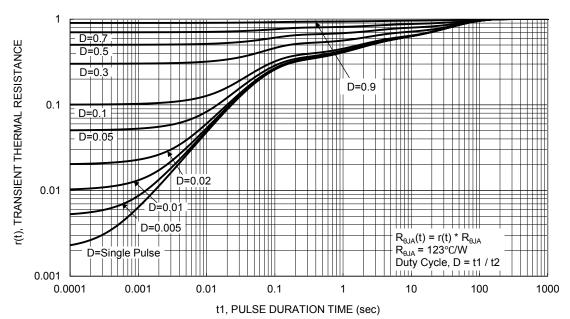


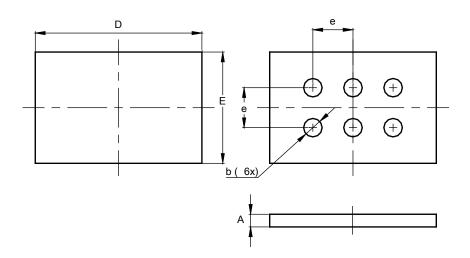
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X3-DSN2718-6

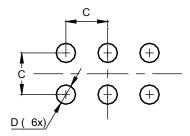


X3-DSN2718-6							
Dim	Min	Max	Тур				
Α	0.16	0.26	0.21				
b	0.27	0.33	0.30				
D	2.65	2.75	2.70				
Е	1.76	1.86	1.81				
e 0.62 0.68 0.65							
All Dimensions in mm							

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

X3-DSN2718-6



Dimensions	Value (in mm)		
С	0.65		
D	0.30		



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